

IN THE CLAIMS

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Please amend claims 1 and 3, and cancel claims 2 and 4 - 8.

B1
1 (Amended). An integrated circuit, comprising:

at least one PNP bipolar transistor, comprising:

an emitter diffusion which has a doping profile that combines a P-well and a P+ diffusion;

a base diffusion comprising a N-well that at least partly underlies said emitter diffusion wherein

said emitter and base diffusions jointly defining an emitter:base ratio of near-junction dopants, measured at 75% and 125% of the emitter-base junction depth, which is greater than two to one.

B2
3 (Amended). The integrated circuit of Claim 1 further comprising a blanket P-type diffusion component having a peak concentration depth more than twice that of said P-well.
